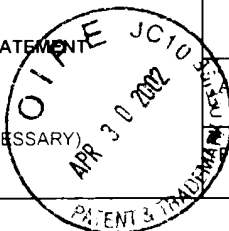


FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX 320A	APPLICATION NO. 10/074,722
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Pomarede et al.	
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
RP	3,900,597	8/19/75	Chruma et al.			
RP	4,217,374	8/12/80	Ovshinsky et al.			
RP	4,237,150	12/2/80	Wiesmann			
RP	4,363,828	12/14/82	Brodsky et al.			
RP	4,379,020	4/5/83	Glaeser et al.			
RP	4,444,812	4/24/84	Gutsche			
RP	4,495,218	1/22/85	Azuma et al.			
RP	4,585,671	4/29/86	Kitagawa et al.			
RP	4,592,933	6/3/86	Meyerson et al.			
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RP	4,684,542	8/4/87	Jasinski et al.			
RP	4,745,083	5/17/88	Inoue et al.			
RP	4,871,416	10/3/89	Fukuda			
RP	4,963,506	10/16/90	Liaw et al.			
RP	5,037,666	8/6/91	Mori			
RP	5,082,696	1/21/92	Sharp			
RP	5,080,933	1/14/92	Gruppen-Shemansky et al.			
RP	5,112,773	5/12/92	Tuttle			
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RP	5,227,329	7/13/93	Kobayashi et al.			
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RP	5,607,724	3/4/97	Beinglass et al.			
RP	5,614,257	3/25/97	Beinglass et al.			

EXAMINER <i>Ron Pomarede</i>	DATE CONSIDERED <i>2-3-03</i>
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Unknown

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RP	6,648,293	7/15/97	Hayama et al.			
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RP	5,695,819	12/9/97	Beinglass et al.			
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RP	5,786,027	7/28/98	Rolfson			
RP	5,789,030	8/4/98	Rolfson			
RP	5,837,580	11/17/98	Thakur et al.			
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RP	5,876,797	3/2/99	Beinglass et al.			
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RP	5,893,949	4/13/99	King et al.			
RP	5,930,106	7/27/99	DeBoer et al.			
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RP	6,027,975	2/22/00	Hergenrother et al.			8/28/98
RP	6,083,810	7/4/00	Obeng et al.			12/5/96
RP	6,197,694 B1	3/6/01	Beinglass			7/31/96

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
RP	54-4066	1/12/79	Japan				✓
RP	57209810 A	12/23/82	Japan			Abstract	
RP	59078918 A	5/8/84	Japan			Abstract	
RP	59078919 A	5/8/84	Japan			Abstract	
RP	60043485 A	3/8/85	Japan			✓	

EXAMINER

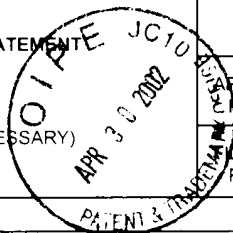
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2-10-03

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FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
RD		61153277 A	7/11/86	Japan			Abstract	
RD		62076612 A	4/8/87	Japan			Abstract	
RD		63003414 A	1/8/88	Japan			Abstract	
RD		63003463 A	1/8/88	Japan			Abstract	
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RD		01268064 A	10/25/89	Japan			Abstract	
RD		02155225 A	6/14/90	Japan			✓	
RD		03091239 A	4/16/91	Japan			✓	
RD		03185817 A	8/13/91	Japan			✓	
RD		03187215 A	8/15/91	Japan			✓	
RD		03292741 A	12/24/91	Japan			Abstract	
RD		04323834 A	11/13/92	Japan			Abstract	
RD		05021378 A	1/29/93	Japan			Abstract	
RD		05062911 A	3/12/93	Japan			✓	
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RD		08242006 A	9/17/96	Japan			Abstract	

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RD	Angermeier et al., "Initial growth processes in the epitaxy of Ge with GeH <sub>4</sub> on oxidized Si substrates," <i>J. Electrochem. Soc.</i> , Vol. 144, No. 2, February 1997, pp 694-697
RD	Bensahel et al., "Industrial single wafer processing of <i>in-situ</i> doped polycrystalline Si and Si <sub>1-x</sub> Ge <sub>x</sub> ," <i>Solid State Technology</i> , March 1998, pp S5-S10.
RD	Bloem, J., "High chemical vapour deposition rates of epitaxial silicon layers," <i>Journal of Crystal Growth</i> , Vol. 18, (1973), pp. 70-76.
RD	Bodnar et al., "Single-wafer Si and SiGe processes for advanced ULSI technologies," <i>Thin Solid Films</i> , Vol. 294, (1997), pp 11-14
RD	Rossi, Ronald C., "Low pressure chemical vapor deposition," <i>Handbook of Thin-Film Deposition Processes and Techniques</i> , pp 80-81
RD	Caymax, et al., "UHV-VLPCVD heteroepitaxial growth of thin SiGe-layers on Si-substrates: Influence of pressure on kinetics and on surface-morphology," <i>Solid State Phenomena</i> , Vol. 32-33, (1993), pp 361-372
RD	Claassen et al., "Deposition of silicon from silane in a low-pressure hot-wall system," <i>Journal of Crystal Growth</i> , Vol. 57, No. 2, (1982), pp. 259-266.
RD	Edwards et al., "Diffusion of Ge along grain boundaries during oxidation of polycrystalline silicon-germanium films," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 319, (1994), pp. 183-188.

EXAMINER <i>for Pomarede</i>	DATE CONSIDERED <i>2-10-03</i>
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
RP	Edwards et al., "Dopant implantation and activation in polycrystalline-SiGe," <i>Mat. Res. Soc. Meeting - Sym. II</i> , Spring 1994, 6 pages.
RP	Eversteyn et al., "Influence of AsH <sub>3</sub> , PH <sub>3</sub> , and B <sub>2</sub> H <sub>6</sub> on the growth rate and resistivity of polycrystalline silicon films deposited from a SiH <sub>4</sub> -H <sub>2</sub> mixture," <i>Growth Rate and Resistivity of Si Films</i> , Vol. 120, No. 1, January 1973, pp. 106-110.
RP	Hernandez et al., "Evidence of interdiffusion effect in stacked polycrystalline SiGe/Si layers for CMOS gate application," <i>Mat. Res. Soc. Meeting</i> , (19_8), 6 pages.
RP	Kamins et al., "Kinetics of silicon-germanium deposition by atmospheric-pressure chemical vapor deposition," <i>Appl. Phys. Lett.</i> , Vol. 59, No. 2, July 8, 1991, pp. 178-180.
RP	King et al., "A polycrystalline Si <sub>1-x</sub> Ge <sub>x</sub> -gate CMOS technology," <i>IEEE</i> , Vol. 253, (1990), pp. 10.4.1-10.4.4.
RP	Li et al., "Rapid thermal chemical vapor deposition of polycrystalline silicon-germanium films on SiO <sub>2</sub> and their properties," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 403, (1996), pp. 333-338.
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RP	Morosanu, C.E., "Thin films by chemical vapour deposition," <i>Thin Films Science and Technology</i> , 7, pp. 48.
RP	Öztürk et al., "Rapid thermal chemical vapor deposition of germanium on silicon and silicon dioxide and new applications of Ge in ULSI technologies," <i>Journal of Electronic Materials</i> , Vol. 19, No. 10, (1990), pp. 1129-1134.
RP	Skotnicki et al., "SiGe gate for highly performant 0.15/018µm CMOS technology," <i>ESSDERC</i> , (1997), pp. 216.

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EXAMINER <i>Rm Pomarede</i>	DATE CONSIDERED <i>2-3-03</i>
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